

BSS138P

60 V, 360 mA N-channel Trench MOSFET Rev. 1 — 2 November 2010

Product data sheet

Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------|----------------------------------|--|--------------|-----|-----|------|
| V_{DS} | drain-source voltage | $T_{amb} = 25 ^{\circ}C$ | - | - | 60 | V |
| V_{GS} | gate-source voltage | $T_{amb} = 25 ^{\circ}C$ | - | - | ±20 | V |
| I_D | drain current | T_{amb} = 25 °C; V_{GS} = 10 V | [1] - | - | 360 | mA |
| R _{DSon} | drain-source on-state resistance | $T_j = 25 ^{\circ}\text{C};$ $V_{GS} = 10 \text{V};$ $I_D = 300 \text{mA}$ | <u>[2]</u> - | 0.9 | 1.6 | Ω |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



^[2] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.01.$

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2. Pinning information

Table 2. Pinning

| Pin Symbol Description 1 G gate 2 S source 3 D drain Simplified outline Graphic symbol | | 9 | | | |
|--|-----|--------|-------------|--------------------|----------------|
| 2 S source 3 D drain | Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 3 D drain | 1 | G | gate | | |
| $1 \square 2$ $G \longrightarrow A$ | 2 | S | source | | D D |
| mp0//b 3 | 3 | D | drain | 1 2 | G Bbb076 S |

3. Ordering information

Table 3. Ordering information

| Type number | Package | Package | | | |
|-------------|----------|--|---------|--|--|
| | Name | Description | Version | | |
| BSS138P | TO-236AB | plastic surface-mounted package; 3 leads | SOT23 | | |

4. Marking

Table 4. Marking codes

| Type number | Marking code ^[1] |
|-------------|-----------------------------|
| BSS138P | AN* |

^{[1] * =} placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

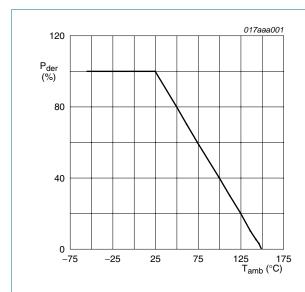
| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------------|----------------------|--|------------|-----|------|
| V_{DS} | drain-source voltage | T _{amb} = 25 °C | - | 60 | V |
| V_{GS} | gate-source voltage | T _{amb} = 25 °C | - | ±20 | V |
| I_D | drain current | $V_{GS} = 10 \text{ V}$ | <u>[1]</u> | | |
| | | T _{amb} = 25 °C | - | 360 | mA |
| | | T _{amb} = 100 °C | - | 230 | mA |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$ | - | 1.2 | Α |

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Table 5. Limiting values ...continued
In accordance with the Absolute Maximum Rating System (IEC 60134).

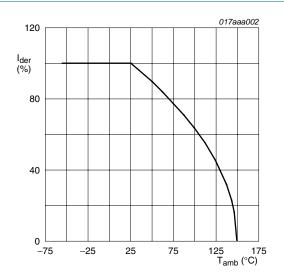
| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------------------|---------------------------|--------------|------|------|
| P_{tot} | total power dissipation | $T_{amb} = 25 ^{\circ}C$ | [2] - | 350 | mW |
| | | | [1] - | 420 | mW |
| | | $T_{sp} = 25 ^{\circ}C$ | - | 1140 | mW |
| Tj | junction temperature | | | 150 | °C |
| T _{amb} | ambient temperature | | –55 | +150 | °C |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Source-d | rain diode | | | | |
| I _S | source current | T _{amb} = 25 °C | <u>[1]</u> _ | 360 | mA |
| | · · · · · · · · · · · · · · · · · · · | | | | |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$

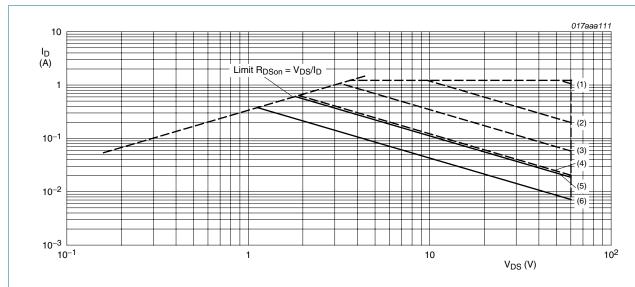
Fig 1. Normalized total power dissipation as a function of ambient temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature

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I_{DM} = single pulse

- (1) $t_p = 100 \mu s$
- (2) $t_p = 1 \text{ ms}$
- (3) $t_p = 10 \text{ ms}$
- (4) $t_D = 100 \text{ ms}$
- (5) DC; $T_{sp} = 25 \, ^{\circ}C$
- (6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 1 cm²

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------|--|-------------|--------------|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance from | in free air | <u>[1]</u> - | 310 | 370 | K/W |
| | junction to ambient | | [2] _ | 260 | 300 | K/W |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | | - | - | 115 | K/W |

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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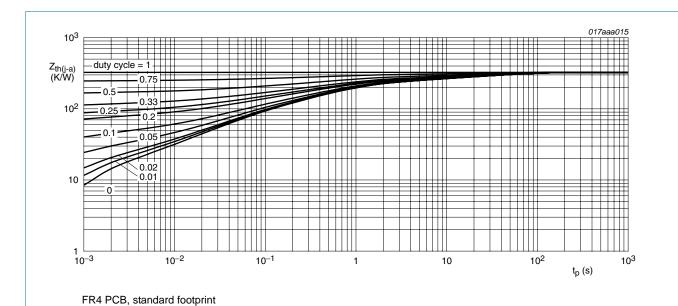


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

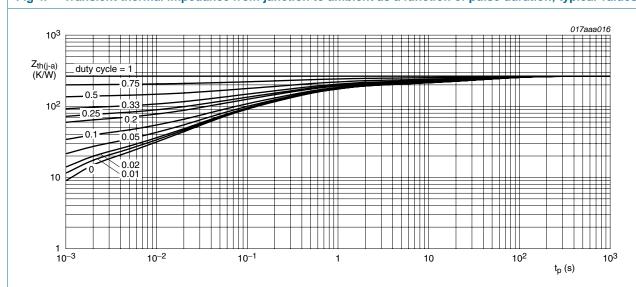


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

FR4 PCB, mounting pad for drain 1 cm²

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7. Characteristics

Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|--------------------------------|--|--------------|------|-----|------|
| Static cha | racteristics | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 10 \ \mu A; \ V_{GS} = 0 \ V$ | 60 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 250 \ \mu A; \ V_{DS} = V_{GS}$ | 0.9 | 1.2 | 1.5 | V |
| I _{DSS} | drain leakage current | $V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$ | | | | |
| | | T _j = 25 °C | - | - | 1 | μΑ |
| | | T _j = 150 °C | - | 10 | 10 | μΑ |
| I _{GSS} | gate leakage current | $V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$ | - | - | 100 | nΑ |
| R _{DSon} | drain-source on-state | | <u>[1]</u> | | | |
| | resistance | $V_{GS} = 5 \text{ V}; I_D = 50 \text{ mA}$ | - | 1 | 2 | Ω |
| | | $V_{GS} = 10 \text{ V}; I_D = 300 \text{ mA}$ | - | 0.9 | 1.6 | Ω |
| g _{fs} | forward transconductance | $V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}$ | <u>[1]</u> _ | 700 | - | mS |
| Dynamic o | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | $I_D = 300 \text{ mA};$ | - | 0.72 | 8.0 | nC |
| Q_{GS} | gate-source charge | $V_{DS} = 30 \text{ V};$ $V_{GS} = 4.5 \text{ V}$ | - | 0.14 | - | nC |
| Q_{GD} | gate-drain charge | V _{GS} = 4.5 V | - | 0.24 | - | nC |
| C _{iss} | input capacitance | $V_{GS} = 0 \text{ V}; V_{DS} = 10 \text{ V};$ | - | 38 | 50 | pF |
| Coss | output capacitance | f = 1 MHz | - | 7 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 4 | - | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 50 \text{ V};$ | - | 2 | 6 | ns |
| t _r | rise time | $R_L = 250 \Omega;$ - $V_{GS} = 10 V;$ | - | 3 | - | ns |
| t _{d(off)} | turn-off delay time | $R_{G} = 6 \Omega$ | - | 9 | 20 | ns |
| t _f | fall time | | - | 4 | - | ns |
| Source-dr | ain diode | | | | | |
| V_{SD} | source-drain voltage | $I_S = 115 \text{ mA}; V_{GS} = 0 \text{ V}$ | 0.47 | 0.75 | 1.1 | V |

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.01.$

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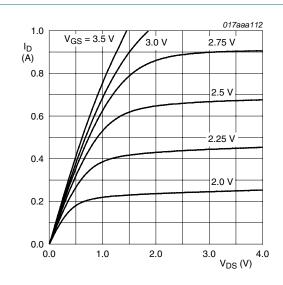
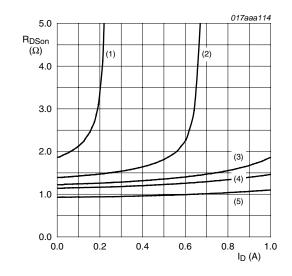


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

 $T_{amb} = 25 \, ^{\circ}C$



T_{amb} = 25 °C

(1) $V_{GS} = 2.0 \text{ V}$

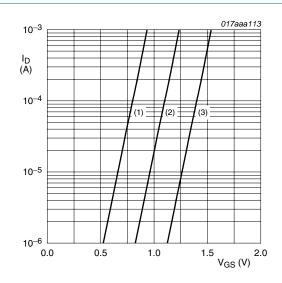
(2) $V_{GS} = 2.5 \text{ V}$

(3) $V_{GS} = 3.0 \text{ V}$

(4) $V_{GS} = 3.5 \text{ V}$

(5) $V_{GS} = 10 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



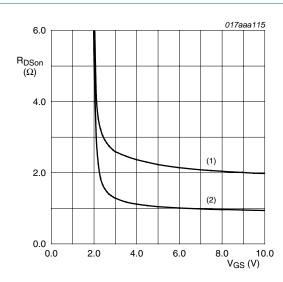
 T_{amb} = 25 °C; V_{DS} = 5 V

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



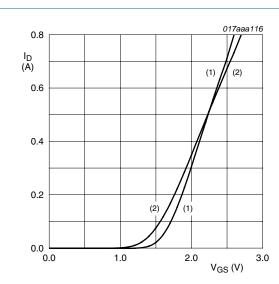
 $I_D = 300 \text{ mA}$

(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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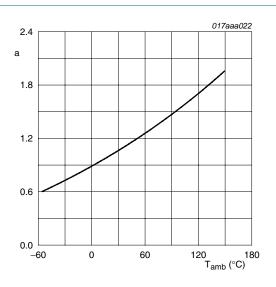


$$V_{DS} > I_D \times R_{DSon}$$

(1)
$$T_{amb} = 25 \,^{\circ}C$$

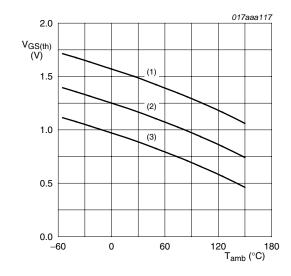
(2)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

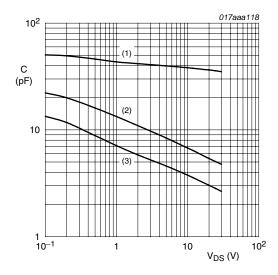
Fig 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

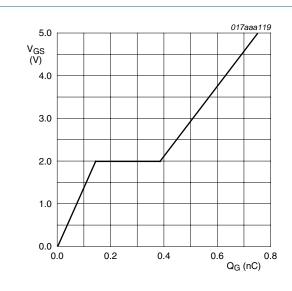
Fig 12. Gate-source threshold voltage as a function of ambient temperature



- (1) C_{iss}
- (2) Coss
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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 I_D = 300 mA; V_{DS} = 30 V; T_{amb} = 25 °C

Fig 14. Gate-source voltage as a function of gate charge; typical values

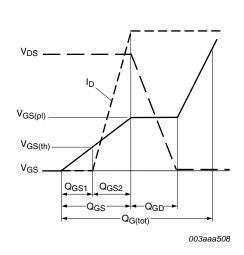
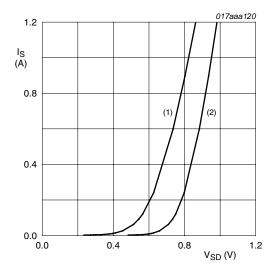


Fig 15. Gate charge waveform definitions



$$V_{GS} = 0 V$$

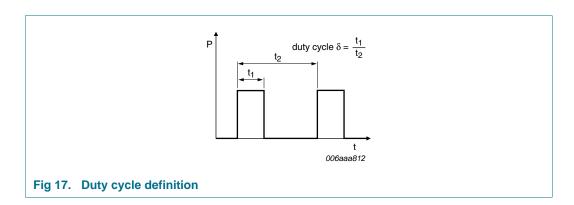
Fig 16. Source current as a function of source-drain voltage; typical values

⁽¹⁾ $T_{amb} = 150 \, ^{\circ}C$

⁽²⁾ $T_{amb} = 25 \, ^{\circ}C$

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8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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9. Package outline

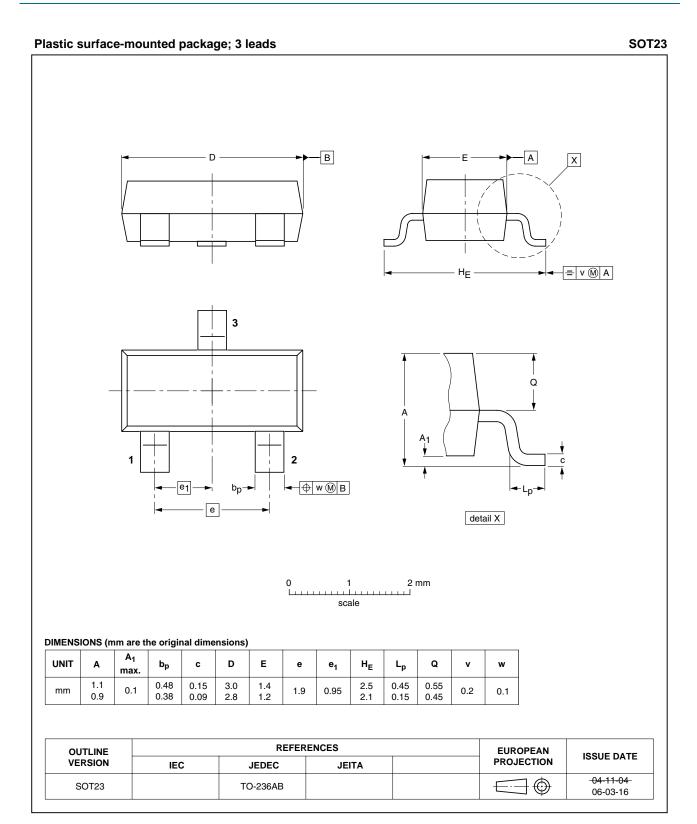
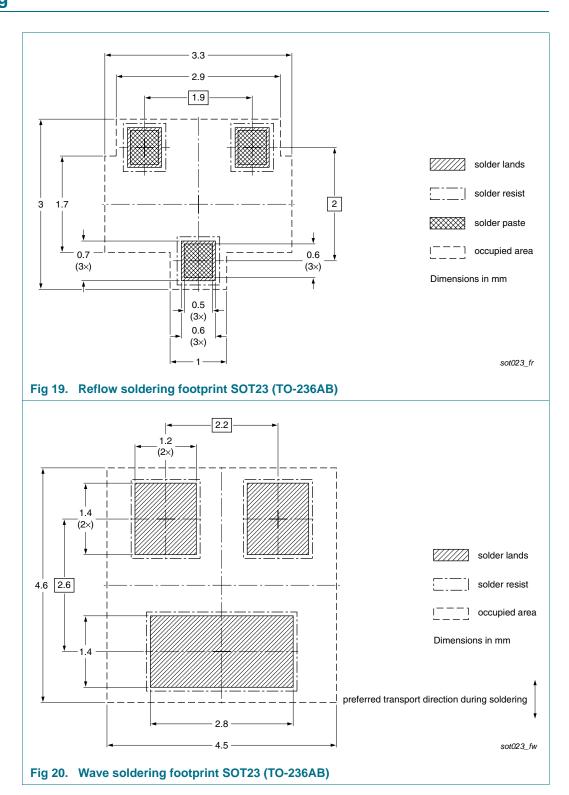


Fig 18. Package outline SOT23 (TO-236AB)

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10. Soldering



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11. Revision history

Table 8. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------|--------------|--------------------|---------------|------------|
| BSS138P v.1 | 20101102 | Product data sheet | - | - |

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12. Legal information

12.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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- [2] The term 'short data sheet' is explained in section "Definitions"
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